BYC10X-600

Rectifier diode, hyperfast Rev. 02 — 16 January 2008

Product data sheet

Product profile 1.

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

Low thermal resistance

Isolated package

1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Reduces switching loss in associated MOSFET

1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies Factor Correction (PFC)
- Half-bridge lighting ballasts

1.4 Quick reference data



■ V_F = 1.32 V (typ)

Pinning information 2.

Table 1.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (k)		. 14
2	anode (a)	mb	k ───── ─ a <i>001aaa020</i>
mb	mounting base; isolated		

SOD113 (2-lead TO-220F)



3. Ordering information

Table 2. Ordering information						
Type number	Package					
	Name	Description	Version			
BYC10X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113			

4. Limiting values

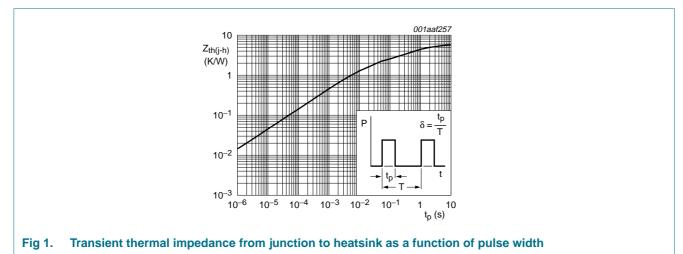
Table 3.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	square waveform; δ = 1.0; $T_h \leq$ 100 $^\circ C$	-	500	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; T_h \leq 37 $^\circ C$	-	10	А
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; T_h \leq 37 $^\circ C$	-	20	А
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	91	А
		t = 8.3 ms; sinusoidal waveform	-	100	А
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
•	with heatsink compound; see <u>Figure 1</u>	-	-	4.8	K/W
	without heatsink compound	-	-	5.9	K/W
thermal resistance from junction to ambient	in free air	-	60	-	K/W
	Parameter thermal resistance from junction to heatsink	ParameterConditionsthermal resistance from junction to heatsinkwith heatsink compound; see Figure 1	ParameterConditionsMinthermal resistance from junction to heatsinkwith heatsink compound; see Figure 1-without heatsink compound-	ParameterConditionsMinTypthermal resistance from junction to heatsink see Figure 1with heatsink compound; see Figure 1without heatsink compound	ParameterConditionsMinTypMaxthermal resistance from junction to heatsink see Figure 1with heatsink compound; see Figure 14.8without heatsink compound5.9



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; f = 50 Hz to 60 Hz; sinusoidal waveform; relative humidity \leq 65 %; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; see <u>Figure 2</u>	-	1.32	2.03	V
		$I_F = 20 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{1000 \text{ C}}$	-	1.64	2.34	V
		I _F = 10 A; see <u>Figure 2</u>	-	1.89	2.9	V
I _R	reverse current	V _R = 600 V	-	9	200	μA
		V_R = 500 V; T_j = 100 °C	-	1.1	3.0	mA
Dynamic o	haracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to } V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ see Figure 3	-	35	55	ns
		I _F = 10 A to V _R = 400 V; dI _F /dt = 500 A/μs; see <u>Figure 3</u>	-	19	-	ns
		I _F = 10 A to V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 100 °C; see <u>Figure 3</u>	-	32	40	ns
I _{RM}	peak reverse recovery current	I _F = 10 A to V _R = 400 V; dI _F /dt = 50 A/µs; T _j = 125 °C; see <u>Figure 3</u>	-	3.0	7.5	A
		$ I_F = 10 \text{ A to } V_R = 400 \text{ V}; \\ dI_F/dt = 500 \text{ A}/\mu\text{s}; \text{ T}_j = 100 ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 3}} $	-	9.5	12	A
V _{FR}	forward recovery voltage	I _F = 10 A; dI _F /dt = 100 A/μs; see <u>Figure 4</u>	-	8	11	V

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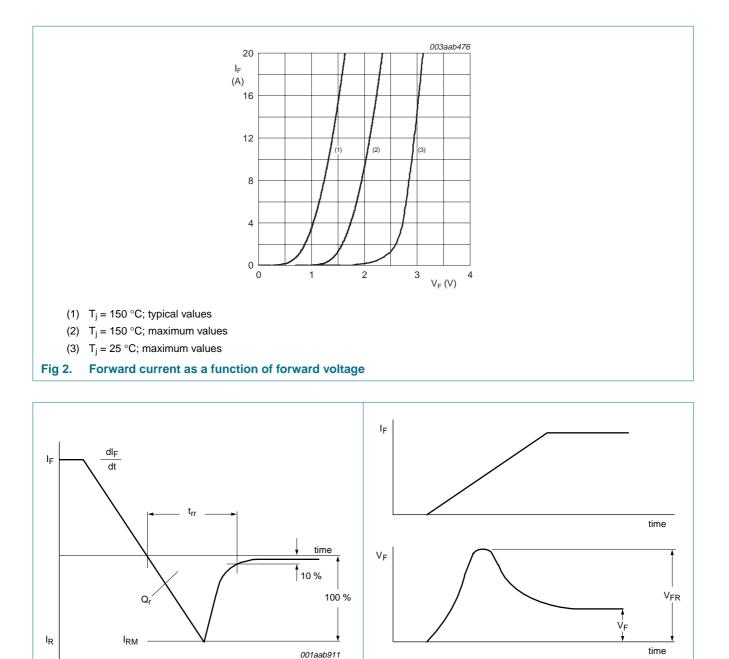


Fig 3. Reverse recovery definitions

Fig 4. Forward recovery definitions

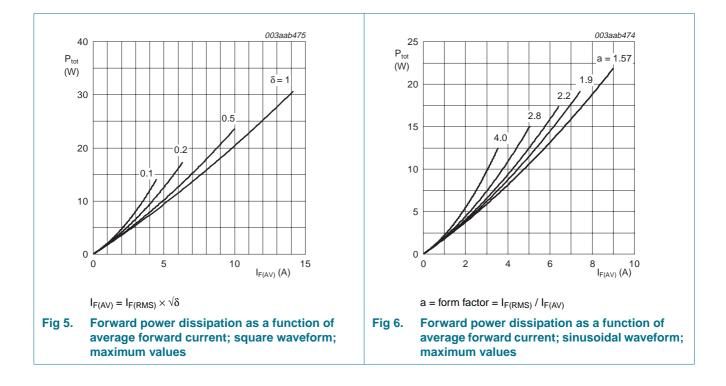
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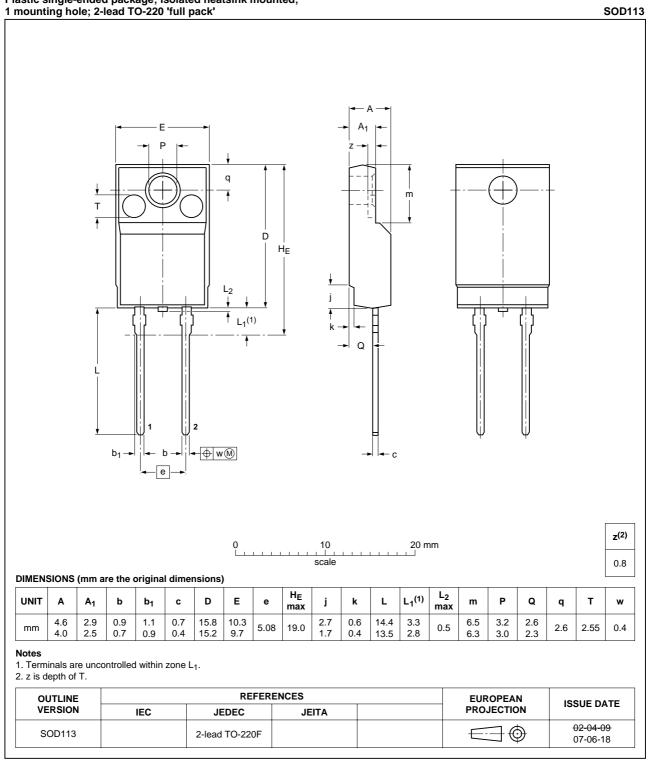
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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

Package outline SOD113 (2-lead TO-220F) Fig 7.

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9. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC10X-600_2	20080116	Product data sheet	-	BYC10X-600_1
Modifications:	 Table 3 "Limitir 	ng values", I _{F(AV)} and I _{FRM} cond	ditions for T _h changed to 37	°C.
BYC10X-600_1	20070831	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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